

# CD74FCT863A

Data sheet acquired from Harris Semiconductor SCHS269

January 1997

# NOT RECOMMENDED FOR NEW DESIGNS Use CMOS Technology

Buffered Inputs

Features

- Typical Propagation Delay: 6.0ns at  $V_{CC} = 5V$ ,  $T_A = 25^{\circ}C$ ,  $C_L = 50pF$
- CD74FCT863A
  - Noninverting
- SCR Latchup Resistant BiCMOS Process and

**BiCMOS FCT Interface Logic,** 9-Bit Bus Transceiver, Three-State

**Circuit Design** 

- Speed of Bipolar FAST™/AS/S
- 48mA Output Sink Current
- Output Voltage Swing Limited to 3.7V at V<sub>CC</sub> = 5V
- Controlled Output Edge Rates
- Input/Output Isolation to V<sub>CC</sub>
- BiCMOS Technology with Low Quiescent Power

# **Ordering Information**

PART NUMBER	TEMP. RANGE (°C)	PACKAGE	PKG. NO.	
CD74FCT863AM	0 to 70	24 Ld SOIC	M24.3	

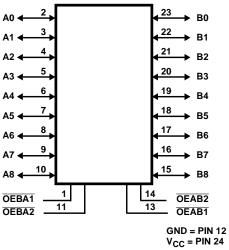
NOTE: When ordering the suffix M package, use the entire part number. Add the suffix 96 to obtain the variant in the tape and reel.

## **Pinout**

CD74FCT863A (SOIC) TOP VIEW

OEBA1 1 24 VCC 23 B0 A0 2 22 B1 A1 | 3 21 B2 20 B3 19 B4 18 B5 17 B6 16 B7 15 B8 A8 10 OEBA2 11 14 OEAB2 13 OEAB1 GND 12

# Functional Diagram



# TRUTH TABLE (Note 1)

INPUTS		OUT	PUTS			
OEBA	OEAB	В	Α	В	Α	FUNCTION
L	Н	L	N/A	N/A	L	B Data to A Bus
L	Н	Н	N/A	N/A	Н	B Data to A Bus
Н	L	N/A	L	L	N/A	A Data to B Bus
Н	L	N/A	Н	Н	N/A	A Data to B Bus
Н	Н	Х	Х	Z	Z	High Z
L	L	-	-	-	-	A Data to B Bus, B Data to A Bus

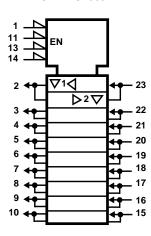
#### NOTE:

1. H= HIGH Voltage Level L = LOW Voltage Level N/A = Not Applicable X = Immaterial

Z = HIGH Impedance

# IEC Logic Symbol

### CD74FCT863A



## CD74FCT863A

# **Absolute Maximum Ratings**

_	
DC Supply Voltage (V <sub>CC</sub> )0.	.5V to 6V
DC Diode Current, I <sub>IK</sub> (For V <sub>I</sub> < -0.5V)	20mA
DC Output Diode Current, I <sub>OK</sub> (for V <sub>O</sub> < -0.5V)	50mA
DC Output Sink Current per Output Pin, IO	70mA
DC Output Source Current per Output Pin, IO	30mA
DC V <sub>CC</sub> Current (I <sub>CC</sub> )	234mA
DC Ground Current (I <sub>GND</sub> )	455mA

## **Thermal Information**

Thermal Resistance (Typical, Note 2)	θ <sub>JA</sub> ( <sup>o</sup> C/W)
SOIC Package	75
Maximum Junction Temperature	150°C
Maximum Storage Temperature Range	65°C to 150°C
Maximum Lead Temperature (Soldering 10s)	300°C
(Lead Tips Only)	

# **Operating Conditions**

Operating Temperature Range, T <sub>A</sub>	
Supply Voltage Range, VCC	4.75V to 5.25V
DC Input Voltage, V <sub>1</sub>	0 to V <sub>CC</sub>
DC Output Voltage, VO	$\dots$ 0 to $\leq$ V <sub>CC</sub>
Input Rise and Fall Slew Rate, dt/dv	0 to 10ns/V

CAUTION: Stresses above those listed in "Absolute Maximum Ratings" may cause permanent damage to the device. This is a stress only rating and operation of the device at these or any other conditions above those indicated in the operational sections of this specification is not implied.

#### NOTE

2.  $\theta_{JA}$  is measured with the component mounted on an evaluation PC board in free air.

# **Electrical Specifications** Commercial Temperature Range $0^{\circ}$ C to $70^{\circ}$ C, $V_{CC}$ Max = 5.25V, $V_{CC}$ Min = 4.75V

					AMBII	ENT TEMI	PERATUR	RE (T <sub>A</sub> )	
		TEST CO	NDITIONS		25	оС	0°C T	O 70°C	
PARAMETER	SYMBOL	V <sub>I</sub> (V)	I <sub>O</sub> (mA)	V <sub>CC</sub> (V)	MIN	MAX	MIN	MAX	UNITS
High Level Input Voltage	V <sub>IH</sub>			4.75 to 5.25	2	-	2	-	V
Low Level Input Voltage	V <sub>IL</sub>			4.75 to 5.25	-	0.8	-	0.8	V
High Level Output Voltage	V <sub>OH</sub>	V <sub>IH</sub> or V <sub>IL</sub>	-15	Min	2.4	-	2.4	-	V
Low Level Output Voltage	V <sub>OL</sub>	V <sub>IH</sub> or V <sub>IL</sub>	48	Min	-	0.55	-	0.55	V
High Level Input Current	I <sub>IH</sub>	Vcc		Max	-	0.1	-	1	μΑ
Low Level Input Current	I <sub>IL</sub>	GND		Max	-	-0.1	-	-1	μΑ
Three-State Leakage Current	lozh	Vcc		Max	-	0.5	-	10	μΑ
	l <sub>OZL</sub>	GND		Max	-	-0.5	-	-10	μΑ
Input Clamp Voltage	V <sub>IK</sub>	V <sub>CC</sub> or GND	-18	Min	-	-1.2	-	-1.2	V
Short Circuit Output Current (Note 3)	los	V <sub>O</sub> = 0 V <sub>CC</sub> or GND		Max	-75	-	-75	-	mA
Quiescent Supply Current, MSI	Icc	V <sub>CC</sub> or GND	0	Max	=	8	-	80	μΑ
Additional Quiescent Supply Current per Input Pin TTL Inputs High, 1 Unit Load	Δl <sub>CC</sub>	3.4V (Note 4)		Max	-	1.6	-	1.6	mA

## NOTES:

- 3. Not more than one output should be shorted at one time. Test duration should not exceed 100ms.
- 4. Inputs that are not measured are at  $V_{\mbox{\footnotesize CC}}$  or GND.
- 5. FCT Input Loading: All inputs are 1 unit load. Unit load is  $\Delta I_{CC}$  limit specified in Static Characteristics Chart, e.g., 1.6mA Max. at  $70^{\circ}C$ .

# CD74FCT863A

# Switching Specifications Over Operating Range FCT Series $t_r$ , $t_f$ = 2.5ns, $C_L$ = 50pF, $R_L$ (Figure 1)

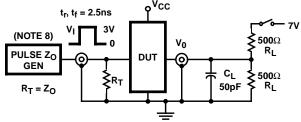
			25°C 0°C TO 70°C			
PARAMETER	SYMBOL	V <sub>CC</sub> (V)	TYP	MIN	MAX	UNITS
Propagation Delays						
Data to Outputs	t <sub>PLH</sub> , t <sub>PHL</sub>	5 (Note 6)	6	1.5	8	ns
Output Enable to Output	t <sub>PZL</sub> , t <sub>PZH</sub>	5	9	1.5	12	ns
Output Disable to Output	t <sub>PLZ</sub> , t <sub>PHZ</sub>	5	7.5	1.5	10	ns
Power Dissipation Capacitance	C <sub>PD</sub> (Note 7)	-	-	-	-	pF
Minimum (Valley) V <sub>OHV</sub> During Switching of Other Outputs (Output Under Test Not Switching)	V <sub>OHV</sub>	5	0.5	-	-	V
Maximum (Peak) V <sub>OLP</sub> During Switching of Other Outputs (Output Under Test Not Switching)	V <sub>OLP</sub>	5	1	-	-	V
Input Capacitance	C <sub>I</sub>	-	-	-	10	pF
Three-State Output Capacitance	CO	-	-	-	15	pF

#### NOTES:

6. 5V: Minimum is at 5.25V for  $0^{\circ}$ C to  $70^{\circ}$ C, Maximum is at 4.75V for  $0^{\circ}$ C to  $70^{\circ}$ C, Typical is at 5V.

7. C<sub>PD</sub>, measured per flip-flop, is used to determine the dynamic power consumption. P<sub>D</sub> (per package) =  $V_{CC} I_{CC} + \Sigma (V_{CC}^2 f_1 C_{PD} + V_0^2 f_0 C_L + V_{CC} \Delta I_{CC} D)$  where:  $V_{CC} = \text{supply voltage}$   $\Delta I_{CC} = \text{flow through current x unit load}$   $C_L = \text{output load capacitance}$  D = duty cycle of input high  $f_O = \text{output frequency}$   $f_1 = \text{input frequency}$ 

# Test Circuits and Waveforms



#### NOTE:

8. Pulse Generator for All Pulses: Rate  $\leq$  1.0MHz;  $Z_{OUT} \leq$  50 $\Omega$ ;  $t_{f}, t_{r} \leq$  2.5ns.

FIGURE 1. TEST CIRCUIT

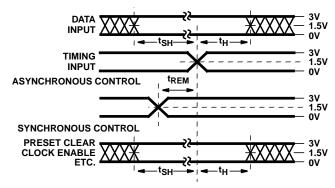


FIGURE 2. SETUP, HOLD, AND RELEASE TIMING

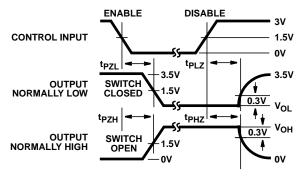


FIGURE 4. ENABLE AND DISABLE TIMING

### **SWITCH POSITION**

TEST	SWITCH
t <sub>PLZ</sub> , t <sub>PZL</sub> , Open Drain	Closed
t <sub>PHZ</sub> , t <sub>PZH</sub> , t <sub>PLH</sub> , t <sub>PHL</sub>	Open

#### **DEFINITIONS:**

C<sub>L</sub> = Load capacitance, includes jig and probe capacitance.

 $R_T$  = Termination resistance, should be equal to  $Z_{\mbox{OUT}}$  of the Pulse Generator.

 $V_{IN} = 0V$  to 3V.

Input:  $t_r = t_f = 2.5$ ns (10% to 90%), unless otherwise specified

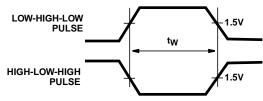


FIGURE 3. PULSE WIDTH

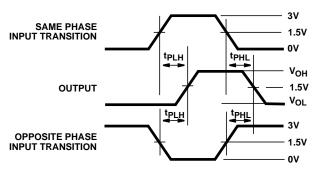
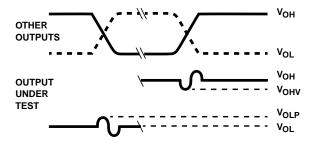


FIGURE 5. PROPAGATION DELAY

# Test Circuits and Waveforms (Continued)



### NOTES:

- 9.  $V_{OLP}$  is measured with respect to a ground reference near the output under test.  $V_{OHV}$  is measured with respect to  $V_{OH}$ .
- 10. Input pulses have the following characteristics:  $P_{RR} \le 1 MHz$ ,  $t_f = 2.5 ns$ ,  $t_f = 2.5 ns$ , skew 1ns.
- 11. R.F. fixture with 700MHz design rules required. IC should be soldered into test board and bypassed with 0.1μF capacitor. Scope and probes require 700MHz bandwidth.

FIGURE 6. SIMULTANEOUS SWITCHING TRANSIENT WAVEFORMS

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